

### 1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection in a DSN0603-2 (SOD962-2) leadless ultra small Surface-Mounted Device (SMD) package.

### 2. Features and benefits

- Average forward current I<sub>F(AV)</sub> ≤ 0.2 A
- Reverse voltage V<sub>R</sub> ≤ 30 V
- Low forward voltage typ. V<sub>F</sub> = 250 mV
- Low reverse current typ. I<sub>R</sub> = 4 μA
- Ultra small and leadless SMD package
- Package height typ. 0.3 mm

## 3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Low power consumption applications
- Ultra high-speed switching
- LED backlight for mobile application

### 4. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>F(AV)</sub>	average forward current	δ = 0.5; f = 20 kHz; T <sub>amb</sub> ≤ 140 °C; square wave	[1]	-	-	0.2	A
		$\delta$ = 0.5; f = 20 kHz; T <sub>sp</sub> ≤ 147 °C; square wave		-	-	0.2	A
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	-	30	V
V <sub>F</sub>	forward voltage	$I_F$ = 10 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>j</sub> = 25 °C		-	250	[tbd]	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = 10 V; T <sub>j</sub> = 25 °C		-	4	[tbd]	μA
t <sub>rr</sub>	reverse recovery time	I <sub>R</sub> = 200 mA; I <sub>F</sub> = 200 mA; I <sub>R(meas)</sub> = 40 mA; T <sub>j</sub> = 25 °C		-	[tbd]	-	ns





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[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode[1]		1 🛃 2
2	А	anode		sym001
			Transparent top view	
			DSN0603-2 (SOD962-2)	

[1] The marking bar indicates the cathode.

# 6. Ordering information

Table 3. Ordering in	formation					
Type number Package						
	Name	Description	Version			
PMEG3002AESF	DSN0603-2	Leadless ultra small package; 2 terminals; body 0.6 x 0.3 x 0.3 mm	SOD962-2			

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
PMEG3002AESF	L

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### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	30	V
l <sub>F</sub>	forward current	T <sub>sp</sub> ≤ 145 °C		-	0.28	А
I <sub>F(AV)</sub>	average forward current	δ = 0.5; f = 20 kHz; T <sub>amb</sub> ≤ 140 °C; square wave	[1]	-	0.2	A
		δ = 0.5; f = 20 kHz; T <sub>sp</sub> ≤ 147 °C; square wave		-	0.2	A
I <sub>FRM</sub>	repetitive peak forward current	$t_p \le 1 \text{ ms}; \delta \le 0.25$		-	1.5	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	4	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	405	mW
			[3]	-	660	mW
			[1]	-	1200	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm<sup>2</sup> each.

### 9. Thermal characteristics

#### Table 6.Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1][2]	-	-	310	K/W
	from junction to ambient		[1][3]	-	-	190	K/W
	ambient		[1][4]	-	-	105	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		[5]	-	-	40	K/W

 For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

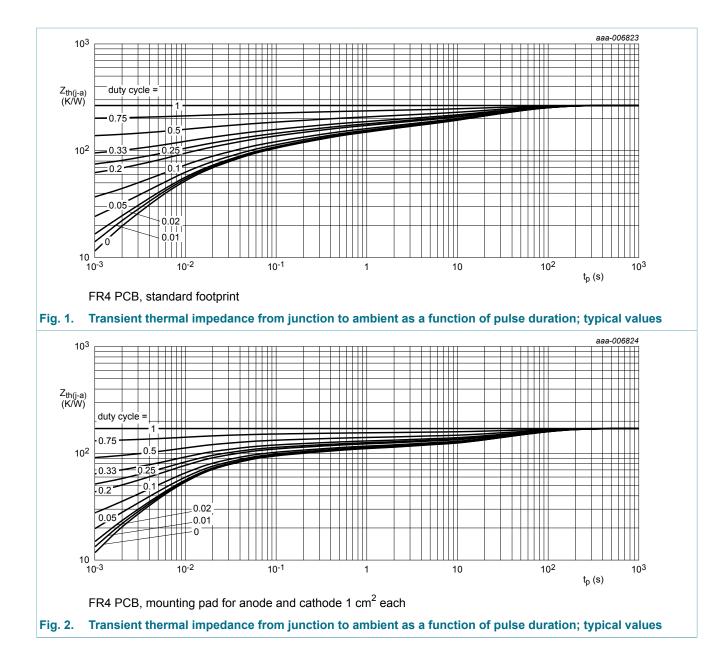
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm<sup>2</sup> each.

- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
  - [5] Soldering point of cathode tab.

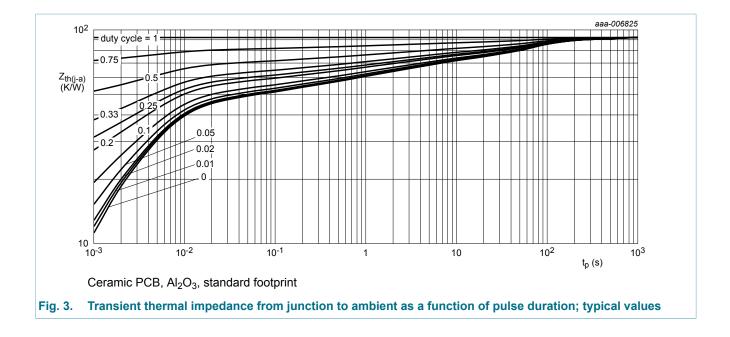
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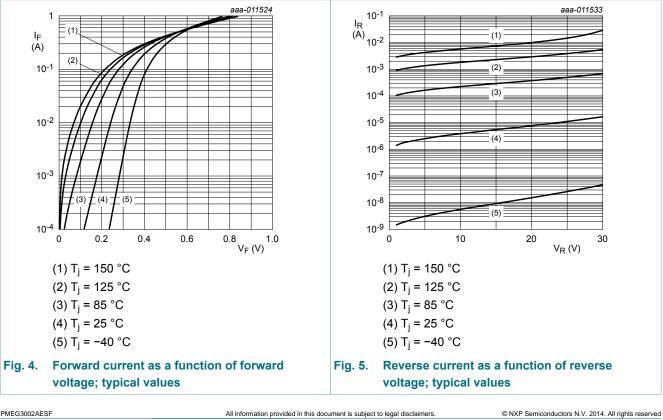
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## **10. Characteristics**

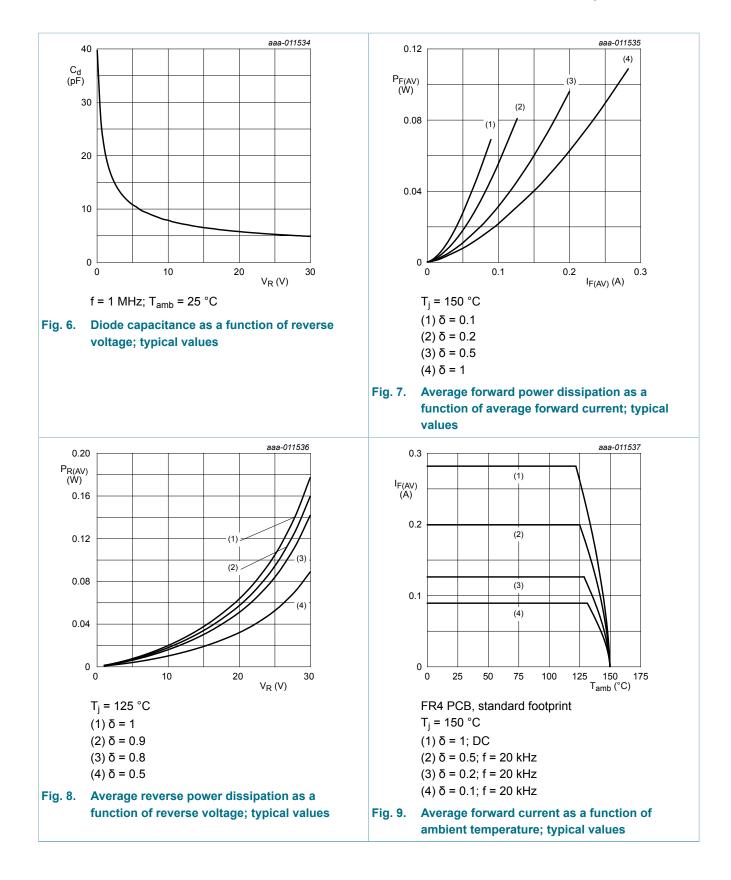
	Characteristics	•		-		
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>F</sub> forwa	forward voltage	$I_F$ = 0.1 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>j</sub> = 25 °C	-	120	[tbd]	mV
		$I_{F}$ = 1 mA; pulsed; $t_{p}$ $\leq$ 300 $\mu s;$ $\delta$ $\leq$ 0.02; $T_{j}$ = 25 $^{\circ} C$	-	180	[tbd]	mV
		$I_F$ = 10 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>j</sub> = 25 °C	-	250	[tbd]	mV
		$I_F$ = 100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>j</sub> = 25 °C	-	350	[tbd]	mV
		I <sub>F</sub> = 200 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>j</sub> = 25 °C	-	405	[tbd]	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = 10 V; T <sub>j</sub> = 25 °C	-	4	[tbd]	μA
		V <sub>R</sub> = 30 V; T <sub>j</sub> = 25 °C	-	20	[tbd]	μA
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	22	-	pF
		V <sub>R</sub> = 10 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	8	-	pF
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 200 mA; I <sub>R</sub> = 200 mA; I <sub>R(meas)</sub> = 40 mA; T <sub>j</sub> = 25 °C	-	[tbd]	-	ns



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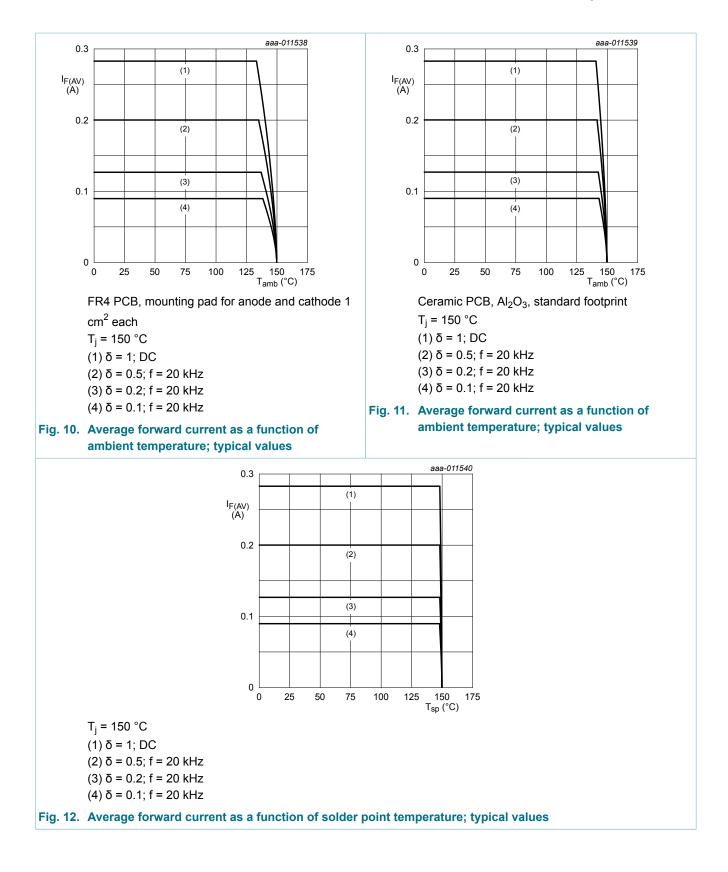
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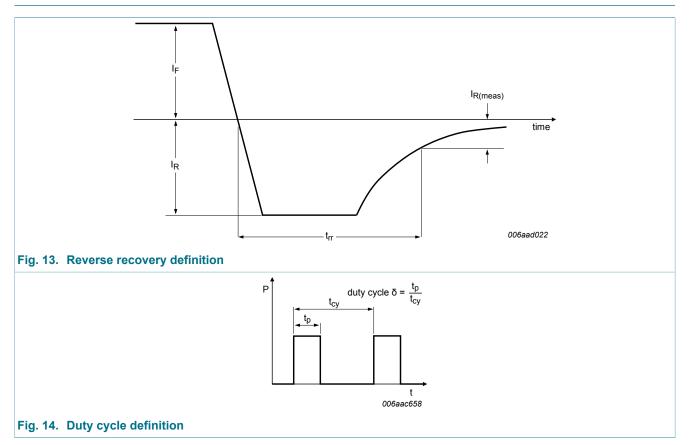


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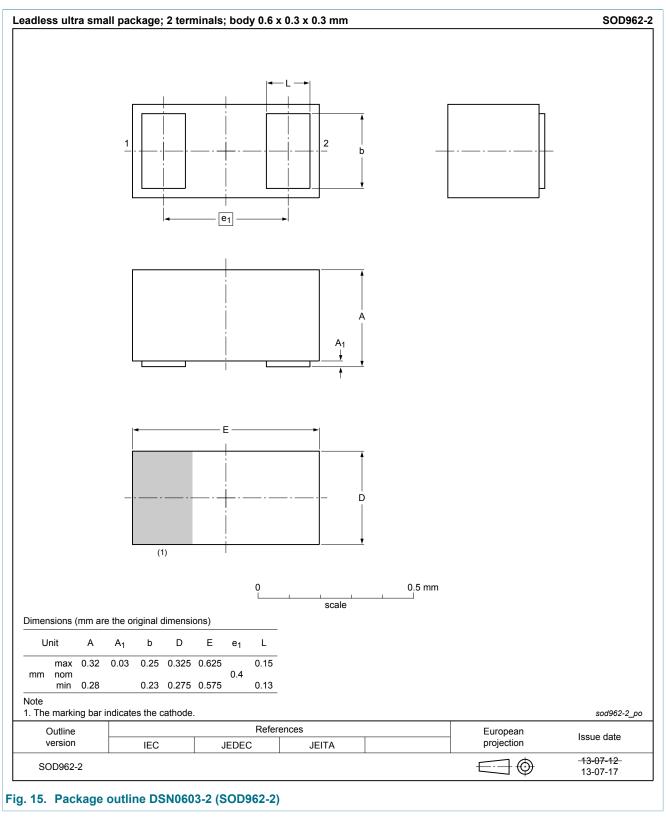
### 11. Test information



The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

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### 12. Package outline



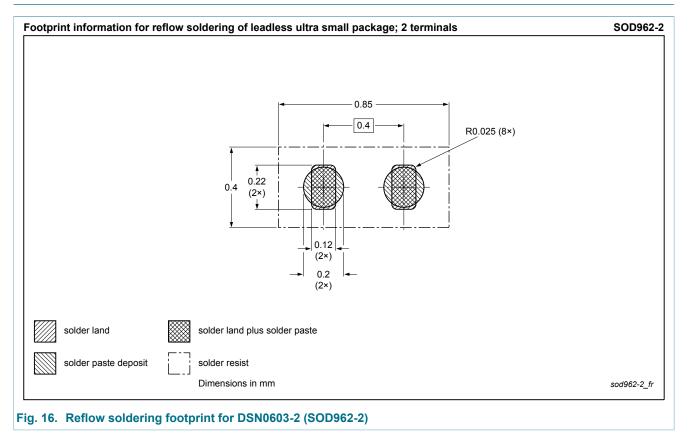
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### 13. Soldering



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## 14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMEG3002AESF v.1	20140408	Preliminary data sheet	-	-			

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### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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